

4V Drive Nch+Nch MOSFET

SH8K32

Structure

Silicon N-channel MOSFET

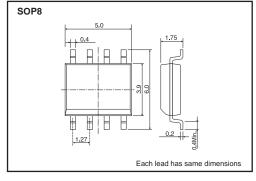
Features

Built-in G-S Protection Diode.
Small surface Mount Package (SOP8).

Application

Switching

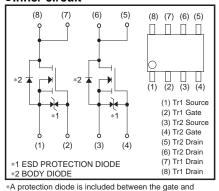
•Dimensions (Unit : mm)



Packaging specifications

	Package	Taping
Туре	Code	TB
	Basic ordering unit (pieces)	2500
SH8K32		0

Inner circuit



A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

•Absolute maximum ratings (Ta=25°C) <It is the same ratings for the Tr1 and Tr2.>

		0	1.116	11.2
Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	60	V
Gate-source voltage		Vgss	±20	V
Drain current	Continuous	ID	±4.5	А
	Pulsed	I _{DP} *1	±18	А
Source current (Body diode)	Continuous	ls	1.0	А
	Pulsed	Isp *1	18	А
Total power dissipation		P _D *2	2.0	W/TOTAL
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

*1 Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board.

•Electrical characteristics (Ta=25°C)

<pre></pre> t is the same characteristics for the Tr1 and Tr2.>			-			
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	-	±10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	V(BR) DSS	60	_	-	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	-	1	μΑ	VDS= 60V, VGS=0V
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	RDS (on)*	-	46	65	mΩ	I _D = 4.5A, V _{GS} = 10V
		-	52	73	mΩ	I _D = 4.5A, V _{GS} = 4.5V
		-	55	77	mΩ	ID= 4.5A, VGS= 4.0V
Forward transfer admittance	Y _{fs} *	4.0	-	_	S	V _{DS} = 10V, I _D = 4.5A
Input capacitance	Ciss	-	500	_	pF	V _{DS} = 10V
Output capacitance	Coss	-	120	-	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	55	-	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	_	12	-	ns	Vdd≒ 30V
Rise time	tr *	_	18	-	ns	D = 2.3A
Turn-off delay time	t _{d (off)} *	_	40	-	ns	Vgs= 10V R∟= 13Ω
Fall time	tr *	-	13	-	ns	R _G =10Ω
Total gate charge	Qg *	_	7.0	10	nC	V _{DD} ≒30V, V _{GS} =5V
Gate-source charge	Q _{gs} *	-	1.6	-	nC	I _D = 4.5A
Gate-drain charge	Q _{gd} *	_	2.5	-	nC	R _L = 6.7Ω, R _G = 10Ω
*Pulsed						

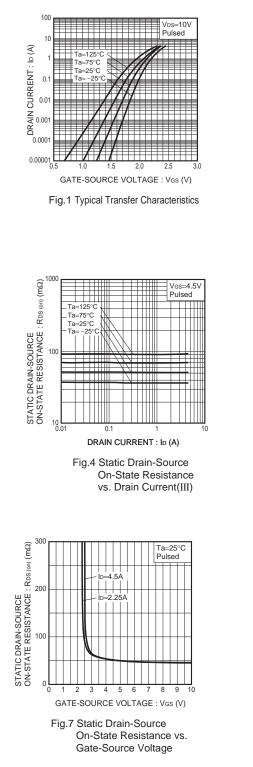
*Pulsed

•Body diode characteristics (Source-Drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd*	-	_	1.2	V	Is=4.5A, V _{GS} =0V
*Pulsed						

•Electrical characteristic curves



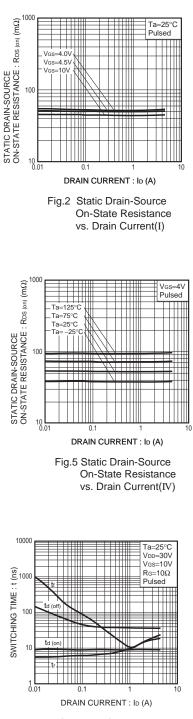
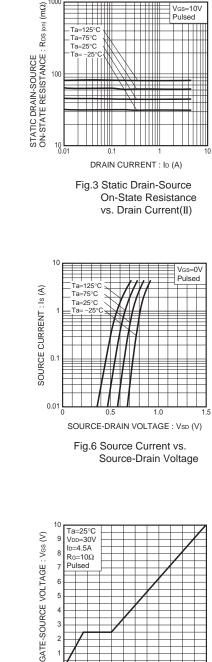


Fig.8 Switching Characteristics



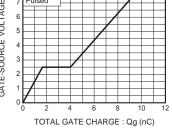
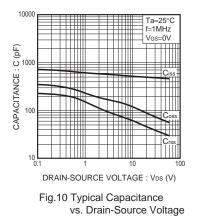


Fig.9 Dynamic Input Characteristics



Measurement circuits

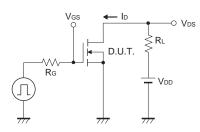


Fig.1-1 Switching Time Test Circuit

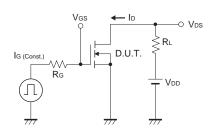


Fig.2-1 Gate Charge Test Circuit

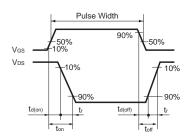


Fig.1-2 Switching Time Waveforms

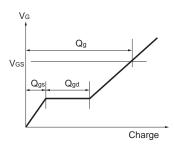


Fig.2-2 Gate Charge Waveform

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